

AMENDMENT TO THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:

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a thin film transistor provided between an element to be driven which operates based on supplied power and which comprises an emissive element which includes an emissive element layer between a first electrode and a second electrode and a power supply line for supplying power to said element to be driven, for controlling the power supplied to said element to be driven; wherein

the thin film transistor and said first electrode of corresponding element to be driven are electrically connected to each other by a wiring layer;

said wiring layer is connected to said thin film transistor through a contact hole formed on-in a first insulation layer which covers said thin film transistor and is connected to said first electrode of said element to be driven formed on a second insulation layer through a contact hole formed on-in said second insulation layer which is formed above said wiring layer to cover said wiring layer;

the contact position between the wiring layer and the thin film transistor is placed to be distant from the contact position between the wiring layer and said element to be driven in the horizontal direction and outside the formation region of said first electrode in the horizontal direction; and

said emissive element layer and said second electrode are layered on said first electrode formed on said second insulation layer.

2. (Currently Amended) A semiconductor device comprising: a thin film transistor provided between an element to be driven which operates based on supplied power and a power supply line for supplying power to said element to be driven, for controlling the power supplied to said element to be driven; wherein

the thin film transistor and corresponding element to be driven are electrically connected to each other by a wiring layer;

the contact position between the wiring layer and the thin film transistor is placed to be distant from the contact position between the wiring layer and said element to be driven;

YKI-0077
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said element to be driven is an emissive element which includes an emissive element layer between a first electrode and a second electrode;

 a contact hole is formed on an insulation layer which is formed above said wiring layer, said wiring layer being connected through the contact hole to said first electrode of said emissive element which is formed on top of said insulation layer and covering said contact hole;

 at least a portion of the contact hole region and at least a portion of said first electrode are filled with a flattening layer of said first electrode to be connected to said wiring layer is filled with a flattening layer; and

 said emissive element layer and said second electrode are formed above said first electrode and said flattening layer ~~filling the contact hole region of said first electrode.~~

3. (Currently Amended) A semiconductor device comprising:

 a thin film transistor for controlling power supplied to an element to be driven which operates based on the supplied power and which includes an emissive element layer between a first electrode and a second electrode, said thin film transistor provided between said element to be driven and a power supply line for supplying power to said element to be driven; wherein

 the thin film transistor and corresponding element to be driven are directly or indirectly and electrically connected to each other at a contact hole formed ~~on-in~~ in an insulation layer for separating said thin film transistor which is formed at a lower layer and said element to be driven;

 said first electrode is formed on said insulation layer to cover said contact hole;

at least a portion of a recess of said first electrode ~~formed in a region at least covering~~ said contact hole is covered by a flattening layer; and

 said emissive element layer is formed above said first electrode and said flattening layer.

4. (Original) A semiconductor device according to claim 1, wherein said element to be driven is an organic electroluminescence element which uses an organic compound in an emissive layer.

5. (Previously Added) A semiconductor device according to claim 2, wherein said element to be driven is an organic electroluminescence element which uses an organic compound in an emissive layer.

6. (Previously Added) A semiconductor device according to claim 3, wherein said element to be driven is an organic electroluminescence element which uses an organic compound in an emissive layer.

7. (New) A semiconductor device according to claim 2, wherein the contact position between the wiring layer and the thin film transistor is placed outside the formation region of said first electrode in the horizontal direction.

8. (New) A semiconductor device comprising:
a thin film transistor for controlling power supplied to an element to be driven which operates based on the supplied power, said thin film transistor provided between said element to be driven and a power supply line for supplying power to said element to be driven; wherein

the thin film transistor and corresponding element to be driven are electrically connected to each other by a wiring layer;

the contact position between the wiring layer and the thin film transistor is placed to be distant from the contact position between the wiring layer and said element to be driven; said element to be driven is an emissive element which includes an emissive element layer between a first electrode and a second electrode;

a first contact hole is formed in a first insulation layer formed below said wiring layer and said wiring layer and said thin film transistor are electrically connected to each other through the first contact hole;

a second contact hole is formed in a second insulation layer formed above said wiring layer and said wiring layer and said first electrode are electrically connected to each other through the second contact hole;

at least a portion of a recess of said first electrode created due to said second contact hole is filled with a flattening layer; and

said emissive element layer and said second electrode are formed above said flattening layer and said first electrode.

9. (New) A semiconductor device according to claim 8, wherein

the contact position between the wiring layer and the thin film transistor is placed outside the formation region of said first electrode in the horizontal direction.

10. (New) A semiconductor device according to claim 8, wherein

said flattening layer is not placed above said first contact hole and is placed above said second contact hole.

11. (New) A semiconductor device according to claim 8, wherein

said flattening layer is placed above said first contact hole and said second contact hole.
